# <u>TOSHIBA</u>

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74HC4066AP,TC74HC4066AF,TC74HC4066AFN,TC74HC4066AFT

#### Quad Bilateral Switch

The TC74HC4066A is a high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate C<sup>2</sup>MOS technology.

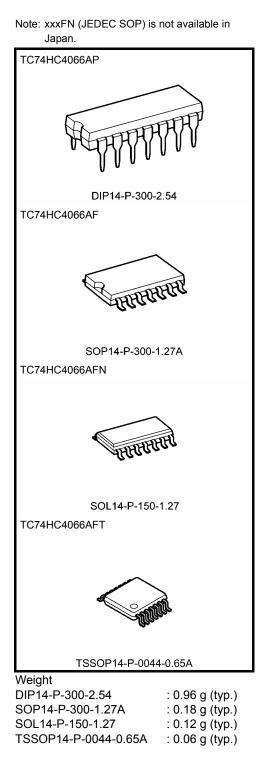
It consists of four independent high speed switches capable of controlling either digital or analog signals while maintaining the CMOS low power dissipation.

Control input (C) is provided to control the switch. The switch turns ON while the C input is high, and the switch turns OFF while low.

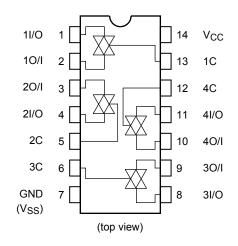
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

#### Features

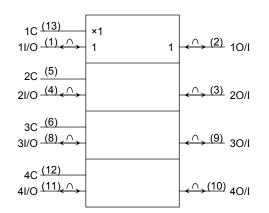
- High speed:  $t_{pd} = 7 \text{ ns}$  (typ.) at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $I_{CC} = 1 \ \mu A \ (max)$  at  $Ta = 25^{\circ}C$
- High noise immunity:  $V_{\text{NIH}} = V_{\text{NIL}} = 28\% V_{\text{CC}}$  (min)
- Low on resistance:  $R_{ON} = 50 \Omega$  (typ.) at  $V_{CC} = 9 V$
- High degree of linearity: THD = 0.05% (typ.) at V<sub>CC</sub> = 5 V
- Pin and function compatible with 4066B



# **Pin Assignment**



# **IEC Logic Symbol**



# Truth Table

Control	Switch Function
Н	On
L	Off

#### Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5 to 13	V
Control input voltage	VIN	-0.5 to V <sub>CC</sub> + 0.5	V
Switch I/O voltage	V <sub>I/O</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Control input diode current	IIК	±20	mA
I/O diode current	IOK	±20	mA
Switch through Current	IOUT	±25	mA
DC V <sub>CC</sub> /ground current	ICC	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T <sub>stg</sub>	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to  $65^{\circ}$ C. From Ta = 65 to  $85^{\circ}$ C a derating factor of -10 mW/°C should be applied up to 300 mW.

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2 to 12	V
Control input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V
Switch I/O voltage	V <sub>I/O</sub>	0 to V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
	tr, tf	0 to 1000 (V <sub>CC</sub> = 2.0 V)	
Input rise and fall time		0 to 500 (V <sub>CC</sub> = 4.5 V)	20
Input rise and fall time		0 to 400 (V <sub>CC</sub> = 6.0 V)	ns
		0 to 250 (V <sub>CC</sub> = 10.0 V)	

#### **Operating Ranges (Note)**

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused control inputs must be tied to either VCC or GND.

# **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol	Test Condition		Ta = 25°C		)	Ta = −40 to 85°C		Unit	
Sharaciensiles Symbol				Min	Тур.	Max	Min	Max	Unit	
			2.0	1.50	—	—	1.50	—		
High-level control	N		4.5	3.15	_	_	3.15	_	v	
input voltage	VIHC	_	9.0	6.30	—	—	6.30	_		
			12.0	8.40	—	—	8.40	—		
			2.0	_	_	0.50	_	0.50		
Low-level control			4.5	—	—	1.35	—	1.35	V	
input voltage	VILC	_	9.0	—	—	2.70	—	2.70	v	
			12.0	—	—	3.60	—	3.60		
		V <sub>IN</sub> = V <sub>IHC</sub>	4.5	_	96	170	_	200		
		$V_{I/O}$ = $V_{CC}$ to GND	9.0	_	55	85	—	100		
		I <sub>I/O</sub> ≤ 1 mA	12.0	—	45	80	_	90		
On resistance	R <sub>ON</sub>		2.0	_	160	_	_	_	Ω	
		$V_{IN} = V_{IHC}$	4.5	_	70	100	_	130		
		$V_{I/O} = V_{CC} \text{ or GND}$ $I_{I/O} \le 1 \text{ mA}$	9.0	_	50	75	_	95		
		II/O ≤ 1 IIIA	12.0	—	45	70	_	90		
Difference of on		V <sub>IN</sub> = V <sub>IHC</sub>	4.5	_	10	_	_	_		
resistance between	ΔR <sub>ON</sub>	$V_{I/O} = V_{CC}$ to GND	9.0	_	5	_	—	_	Ω	
switches		I <sub>I/O</sub> ≤ 1 mA	12.0	_	5	_	_	_		
Input/output leakage		V <sub>OS</sub> = V <sub>CC</sub> or GND								
current	IOFF	$V_{IS}$ = GND or $V_{CC}$	12.0	_	-   _	±100	—	±1000	nA	
(switch off)		V <sub>IN</sub> = V <sub>ILC</sub>								
Switch input leakage										
current	I <sub>IZ</sub>	V <sub>OS</sub> =V <sub>CC</sub> or GND		_	_	±100	_	±1000	nA	
(switch on, output open)		V <sub>IN</sub> = V <sub>IHC</sub>								
Control input current	l <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND	12.0	—	—	±100	—	±1000	nA	
			6.0	_	_	1.0	_	10.0		
Quiescent supply current	ICC	V <sub>IN</sub> = V <sub>CC</sub> or GND	9.0	—	—	4.0	_	40.0	μA	
			12.0	_	_	8.0	_	80.0		

# AC Characteristics ( $C_L$ = 50 pF, input: $t_r$ = $t_f$ = 6 ns)

Characteristics	Symbol Test Condition			Ta = 25°C		Ta = −40 to 85°C		Unit	
		VCC (V)	Min	Тур.	Max	Min	Max	Offic	
			2.0	_	10	50	_	65	pF
Phase difference between input and	ФІ-О		4.5	_	4	10	—	13	
output	ΨΙ-Ο	_	9.0	—	3	8	—	10	
			12.0		3	7	—	9	
			2.0	—	18	100	—	125	
Output enable time	t <sub>pZL</sub>	R <sub>L</sub> = 1 kΩ	4.5	_	8	20	—	25	pF
	t <sub>pZH</sub>		9.0	—	6	12	—	22	
			12.0		6	12	—	18	
	t <sub>pLZ</sub> t <sub>pHZ</sub>	R <sub>L</sub> = 1 kΩ	2.0		20	115	—	145	pF
Output disable time			4.5	_	10	23	—	29	
			9.0	—	8	20	—	25	
			12.0		8	18	—	22	
	С	R <sub>L</sub> = 1 kΩ	2.0	—	30	—	—	—	MHz
Maximum control		$C_L = 15 \text{ pF}$ V <sub>OUT</sub> = 1/2 V <sub>CC</sub>	4.5	_	30	—	—	—	
input frequency			9.0	_	30	—	—	—	
		V001 - 1/2 VCC	12.0		30	—	—	—	
Control input capacitance	C <sub>IN</sub>	_		—	5	10	_	10	pF
Switch terminal capacitance	C <sub>I/O</sub>	_		_	6	_	_	_	pF
Feed through capacitance	C <sub>IOS</sub>	_		_	0.5	_	_	_	pF
Power dissipation capacitance	C <sub>PD</sub>		(Note)	—	15	—	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4$  (per channel)

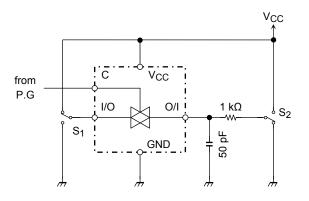
#### Analog Switch Characteristics (GND = 0 V, Ta = 25°C) (Note)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Тур.	Unit
Sine wave distortion (T.H.D)		$f_{IN}$ = 1 kHz, V <sub>IN</sub> = 4 V <sub>p-p</sub> , @V <sub>CC</sub> = 4.5 V R <sub>L</sub> = 10 kΩ, V <sub>IN</sub> = 8 V <sub>p-p</sub> , @V <sub>CC</sub> = 9.0 V C <sub>L</sub> = 50 pF	4.5 9.0	0.05 0.04	%
Frequency response (switch on)	f <sub>max</sub>	Adjust $f_{IN}$ voltage to obtain 0dBm at V <sub>OS</sub> Increase $f_{IN}$ frequency until dB meter reads -3dB $R_L = 50 \Omega$ , $C_L = 10 pF$ $f_{IN} = 1 MHz$ , sine wave	4.5 9.0	200 200	MHz
Feedthrough attenuation (switch off)		Vin is centered at V <sub>CC</sub> /2 Adjust input for 0dBm $R_L = 600 \Omega$ , $C_L = 50 pF$ $f_{IN} = 1 MHz$ , sine wave	4.5 9.0	-60 -60	dB
Crosstalk (control input to signal output)		$R_L$ = 600 Ω, $C_L$ = 50 pF $f_{ N}$ = 1 MHz, square wave ( $t_r$ = $t_f$ = 6 ns)	4.5 9.0	60 100	mV
Crosstalk (between any switches)		Adjust V <sub>IN</sub> to obtain 0dBm at input R <sub>L</sub> = 600 $\Omega$ , C <sub>L</sub> = 50 pF f <sub>IN</sub> = 1 MHz, sine wave	4.5 9.0	-60 -60	dB

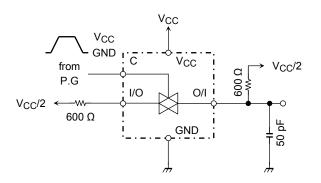
Note: These characteristics are determined by design of devices.

# **Switching Characteristics Test Circuits**

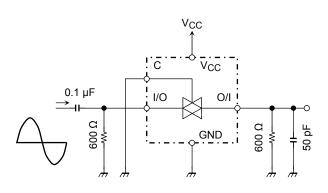
1. t<sub>pLZ</sub>, t<sub>pHZ</sub>, t<sub>pZL</sub>, t<sub>pZH</sub>

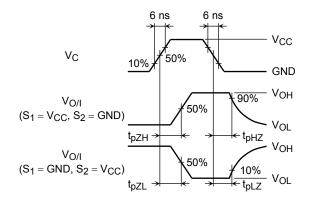


2. Cross Talk (control input-switch output) fIN = 1 MHz duty = 50% tr = tf = 6 ns



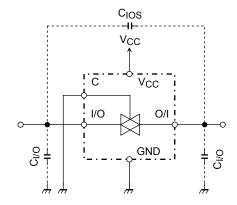
#### 3. Feedthrough Attenuation



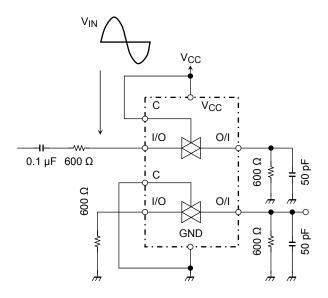


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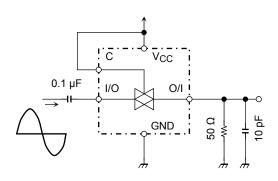
# 4. $C_{IOS}, C_{I/O}$



#### 5. Crosstalk (between any two switches)



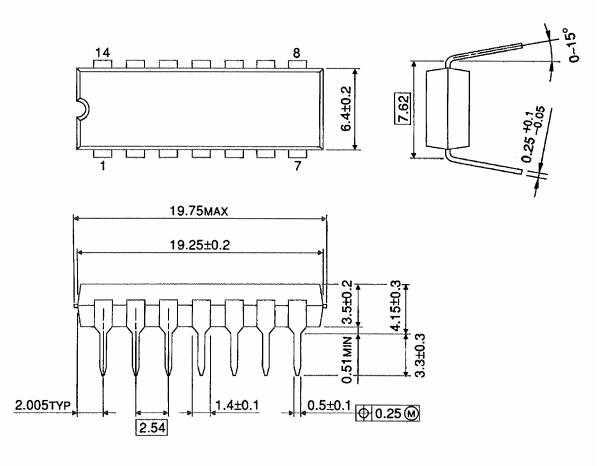
6. Frequency Response (switch on)



#### **Package Dimensions**

DIP14-P-300-2.54

Unit : mm



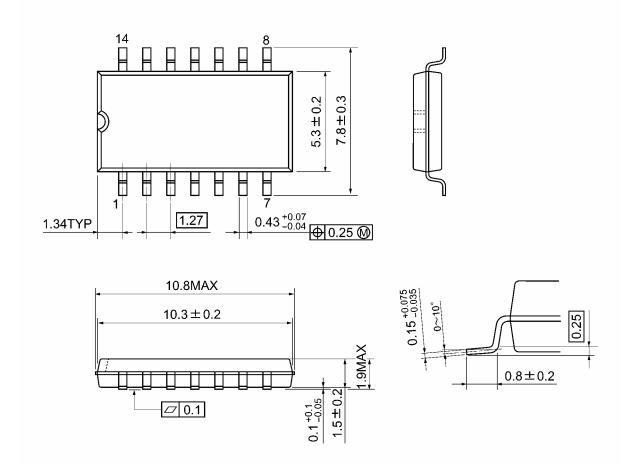
Weight: 0.96 g (typ.)



#### **Package Dimensions**

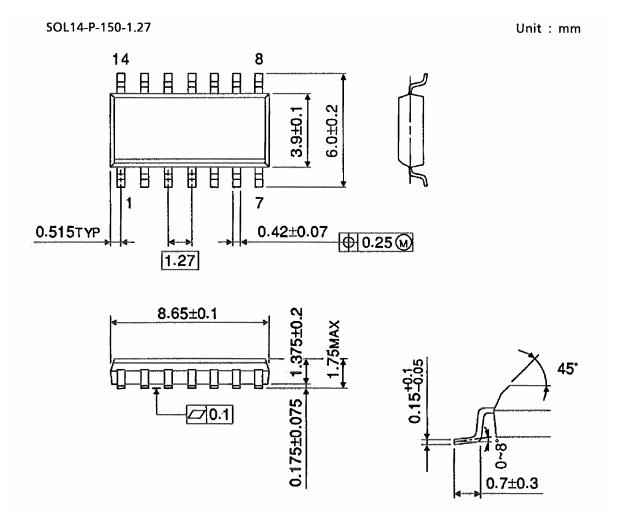
SOP14-P-300-1.27A

Unit: mm



Weight: 0.18 g (typ.)

# Package Dimensions (Note)



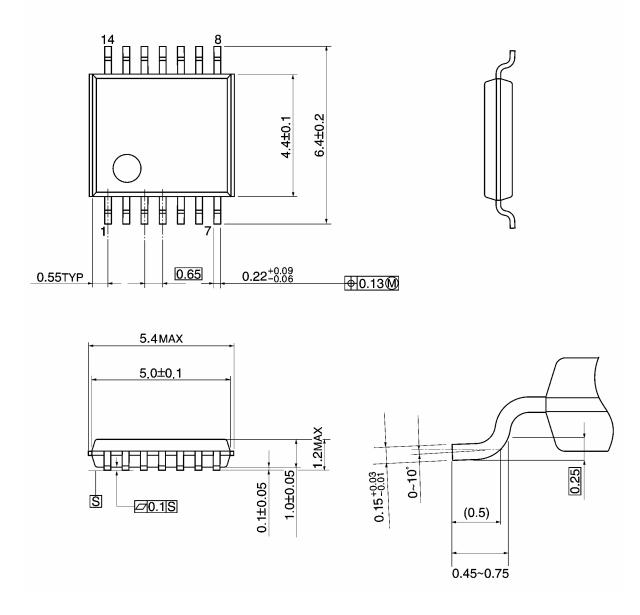
Note: This package is not available in Japan.

Weight: 0.12 g (typ.)

# Package Dimensions

TSSOP14-P-0044-0.65A

Unit: mm



Weight: 0.06 g (typ.)

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20070701-EN GENERAL

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